

SOT23 NPN SILICON PLANAR HIGH GAIN MEDIUM POWER TRANSISTOR

FMMTL618

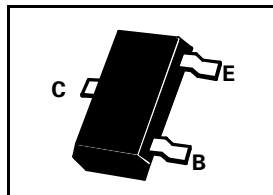
ISSUE 1 – NOVEMBER 1997

FEATURES

Very low equivalent on-resistance; $R_{CE(sat)}=140m\Omega$ at 1.25A

COMPLEMENTARY TYPE – FMMTL718

PARTMARKING DETAIL – L68



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	1.25	A
Peak Pulse Current	I_{CM}	4	A
Base Current	I_B	200	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	500	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

FMMTL618

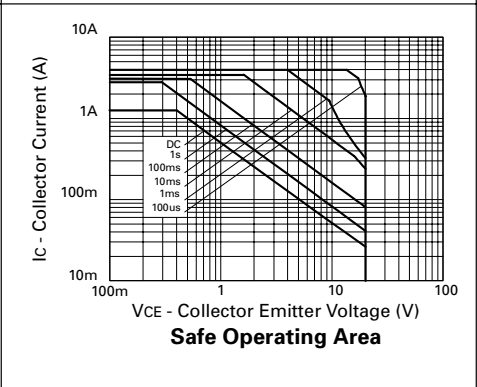
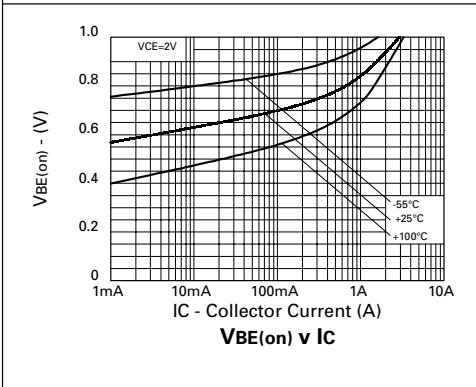
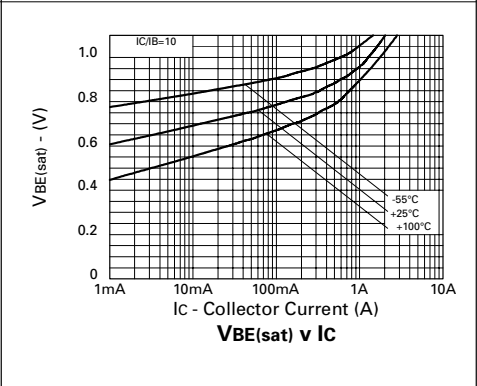
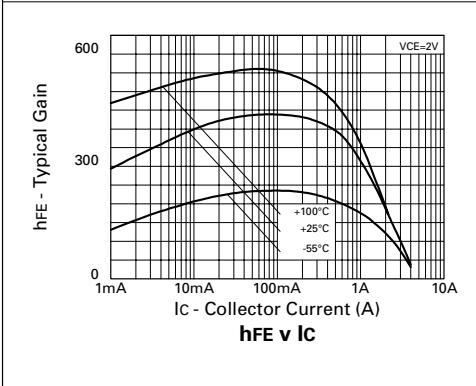
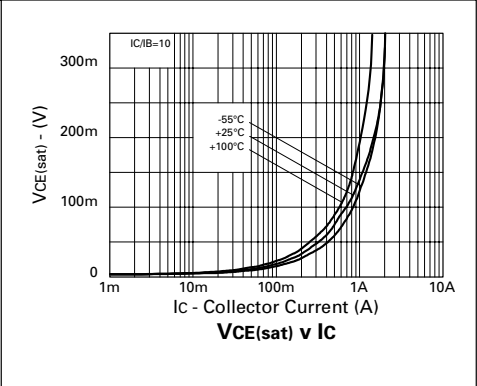
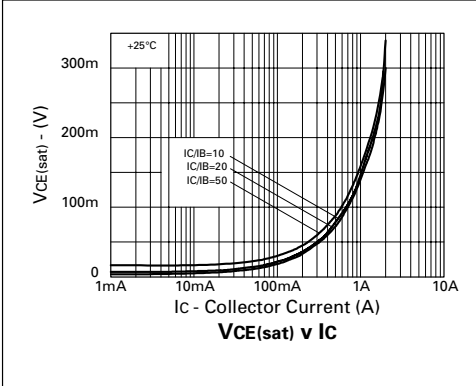
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	105		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	20	30		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	8.5		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			10	nA	$V_{CE}=16\text{V}$
Emitter Cut-Off Current	I_{EBO}			10	nA	$V_{EB}=4\text{V}$
Collector Cut-Off Current	I_{CES}			10	nA	$V_{CE}=16\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		18 80 130 170 260	35 160 200 280 350	mV mV mV mV mV	$I_C=100\text{mA}, I_B=10\text{mA}^*$ $I_C=500\text{mA}, I_B=25\text{mA}^*$ $I_C=1\text{A}, I_B=100\text{mA}^*$ $I_C=1.25\text{A}, I_B=100\text{mA}^*$ $I_C=2\text{A}, I_B=200\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1000	1100	mV	$I_C=1.25\text{A}, I_B=100\text{mA}^*$
Base-Emitter Turn On Voltage	$V_{BE(on)}$		850	1000	mV	$I_C=1.25\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	200 300 250 200 100 50	400 440 400 300 190 100			$I_C=10\text{mA}, V_{CE}=2\text{V}$ $I_C=200\text{mA}, V_{CE}=2\text{V}^*$ $I_C=500\text{mA}, V_{CE}=2\text{V}^*$ $I_C=1\text{A}, V_{CE}=2\text{V}^*$ $I_C=2\text{A}, V_{CE}=2\text{V}^*$ $I_C=3\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T		195		MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=100\text{MHz}$
Collector-Base Breakdown Voltage	C_{obo}		9	12	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Switching times	t_{on} t_{off}		72 388		ns ns	$I_C=1\text{A}, V_{CC}=10\text{V}$ $I_{B1}=-I_{B2}=10\text{mA}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

FMMTL618

TYPICAL CHARACTERISTICS





LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.